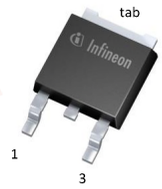
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MOSFET

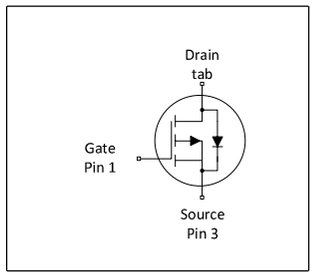
OptiMOS™ Power-Transistor, -150 V

D-PAK



Features

- P-channel
- Very low on-resistance $R_{DS(on)}$ @ V_{GS}= 4.5 V
- 100% avalanche tested
- Logic level
- Enhancement mode
- Pb-free lead plating; RoHS compliant
- Halogen-free according to IEC61249-2-21



Product validation

Fully qualified according to JEDEC for Industrial Applications

Table 1 Key Performance Parameters

Parameter	Value	Unit
V_{DS}	-150	V
$R_{DS(on),max}$	420	mΩ
I_D	-9.0	A
Q_{oss}	-12	nC
Q_G	-43	nC

Type / Ordering Code	Package	Marking	Related Links
IPD42DP15LM	PG-TO252-3	42DP15LM	-

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1 Maximum ratings

at T_A=25 °C, unless otherwise specified

Table 2 Maximum ratings

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Continuous drain current[1]	I_D	- - - -	- - - -	-9.0 -6.3 -6.3 -1.7	A	V_{GS}=-10 V, T_C=25 °C V_{GS}=-10 V, T_C=100 °C V_{GS}=-4.5 V, T_C=100 °C V_{GS}=-4.5 V,T_A=25°C,R_{thJA}=50°C/W[2]
Pulsed drain current[3]	$I_{D,pulse}$	-	-	-36	A	T_A=25 °C
Avalanche energy, single pulse[4]	E_{AS}	-	-	290	mJ	I_D=-8.2 A, R_{GS}=25 Ω
Gate source voltage	V_{GS}	-20	-	20	V	-
Power dissipation	P_{tot}	- -	- -	83 3.0	W	T_C=25 °C T_A=25 °C, R_{THJA}=50 °C/W[2]
Operating and storage temperature	T_j, T_{stg}	-55	-	175	°C	IEC climatic category; DIN IEC 68-1: 55/175/56

2 Thermal characteristics

Table 3 Thermal characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Thermal resistance, junction - case	R_{thJC}	-	-	1.8	°C/W	-
Thermal resistance, junction - ambient, 6 cm² cooling area	R_{thJA}	-	-	50	°C/W	-
Thermal resistance, junction - ambient, minimal footprint[2]	R_{thJA}	-	-	75	°C/W	-

[1] Rating refers to the product only with datasheet specified absolute maximum values, maintaining case temperature as specified. For other case temperatures please refer to Diagram 2. De-rating will be required based on the actual environmental conditions.
[2] Device on 40 mm x 40 mm x 1.5 mm epoxy PCB FR4 with 6 cm² (one layer, 70 µm thick) copper area for drain connection. PCB is vertical in still air.
[3] See Diagram 3 for more detailed information
[4] See Diagram 13 for more detailed information

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3 Electrical characteristics

at T_j=25 °C, unless otherwise specified

Table 4 Static characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Drain-source breakdown voltage	$V_{(BR)DSS}$	-150	-	-	V	V_{GS}=0 V, I_D=-1 mA
Gate threshold voltage	$V_{GS(th)}$	-1.0	-1.5	-2.0	V	V_{DS}=V_{GS}, I_D=-1040 µA
Zero gate voltage drain current	I_{DSS}	- -	-0.1 -10	-1.0 -100	µA	V_{DS}=-150 V, V_{GS}=0 V, T_j=25 °C V_{DS}=-150 V, V_{GS}=0 V, T_j=125 °C
Gate-source leakage current	I_{GSS}	-	-10	-100	nA	V_{GS}=-20 V, V_{DS}=0 V
Drain-source on-state resistance	$R_{DS(on)}$	- -	334.5 326	420 430	mΩ	V_{GS}=-10 V, I_D=-8.2 A V_{GS}=-4.5 V, I_D=-6.6 A
Gate resistance	R_G	-	5.0	-	Ω	-
Transconductance	g_{fs}	-	18	-	S	|V_{DS}|≥2|I_D|$R_{DS(on)max}$, I_D=-8.2 A

Table 5 Dynamic characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Input capacitance[1)]	C_{iss}	-	1600	2100	pF	V_{GS}=0 V, V_{DS}=-75 V, f=1 MHz
Output capacitance[1)]	C_{oss}	-	67	87	pF	V_{GS}=0 V, V_{DS}=-75 V, f=1 MHz
Reverse transfer capacitance[1)]	C_{rss}	-	16	28	pF	V_{GS}=0 V, V_{DS}=-75 V, f=1 MHz
Turn-on delay time	$t_{d(on)}$	-	15.58	-	ns	V_{DD}=-75 V, V_{GS}=-4.5 V, I_D=-8.2 A, $R_{G,ext}$=1.6 Ω
Rise time	t_r	-	36.68	-	ns	V_{DD}=-75 V, V_{GS}=-4.5 V, I_D=-8.2 A, $R_{G,ext}$=1.6 Ω
Turn-off delay time	$t_{d(off)}$	-	26.8	-	ns	V_{DD}=-75 V, V_{GS}=-4.5 V, I_D=-8.2 A, $R_{G,ext}$=1.6 Ω
Fall time	t_f	-	29.33	-	ns	V_{DD}=-75 V, V_{GS}=-4.5 V, I_D=-8.2 A, $R_{G,ext}$=1.6 Ω

[1)] Defined by design. Not subject to production test.

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Table 6 Gate charge characteristics[1)]

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Gate to source charge	Q_{gs}	-	-4.7	-	nC	V_{DD}=-75 V, I_D=-8.2 A, V_{GS}=0 to -4.5 V
Gate charge at threshold	$Q_{g(th)}$	-	-2.4	-	nC	V_{DD}=-75 V, I_D=-8.2 A, V_{GS}=0 to -4.5 V
Gate to drain charge[2)]	Q_{gd}	-	-10.9	-16.4	nC	V_{DD}=-75 V, I_D=-8.2 A, V_{GS}=0 to -4.5 V
Switching charge	Q_{sw}	-	-13.3	-	nC	V_{DD}=-75 V, I_D=-8.2 A, V_{GS}=0 to -4.5 V
Gate charge total[2)]	Q_g	-	-21	-26	nC	V_{DD}=-75 V, I_D=-8.2 A, V_{GS}=0 to -4.5 V
Gate plateau voltage	$V_{plateau}$	-	-3	-	V	V_{DD}=-75 V, I_D=-8.2 A, V_{GS}=0 to -4.5 V
Gate charge total	Q_g	-	-43	-	nC	V_{DD}=-75 V, I_D=-8.2 A, V_{GS}=0 to -10 V
Output charge[2)]	Q_{oss}	-	-12.2	-16.2	nC	V_{DS}=-75 V, V_{GS}=0 V

Table 7 Reverse diode

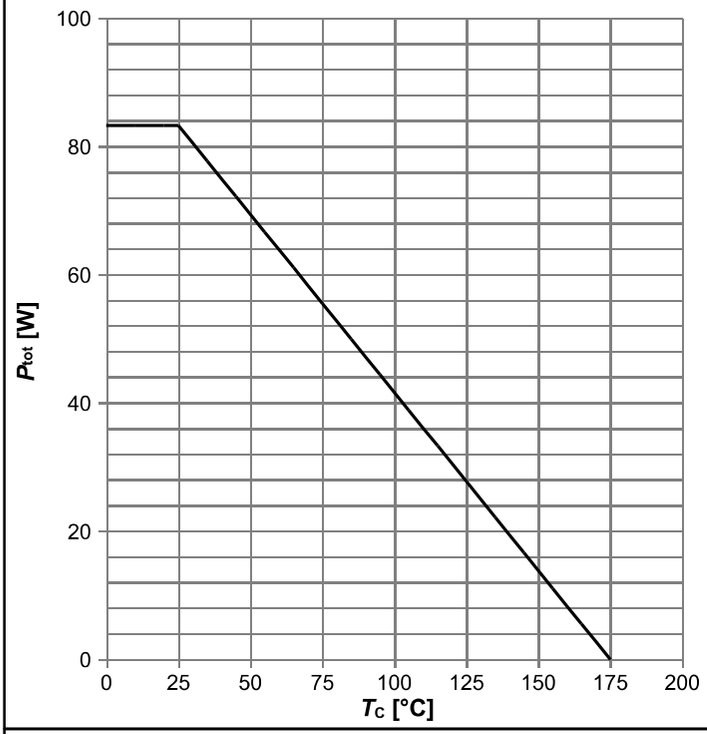
Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Diode continuous forward current	I_S	-	-	-9.2	A	T_C=25 °C
Diode pulse current	$I_{S,pulse}$	-	-	-37	A	T_C=25 °C
Diode forward voltage	V_{SD}	-	-0.84	-1.2	V	V_{GS}=0 V, I_F=-8.2 A, T_j=25 °C
Reverse recovery time[2)]	t_{rr}	-	74.3	148.6	ns	V_R=-75 V, I_F=-8.2 A, di_F/dt=-100 A/µs
Reverse recovery charge[2)]	Q_{rr}	-	273.8	547.6	nC	V_R=-75 V, I_F=-8.2 A, di_F/dt=-100 A/µs

[1)] See ″Gate charge waveforms″ for parameter definition
[2)] Defined by design. Not subject to production test.

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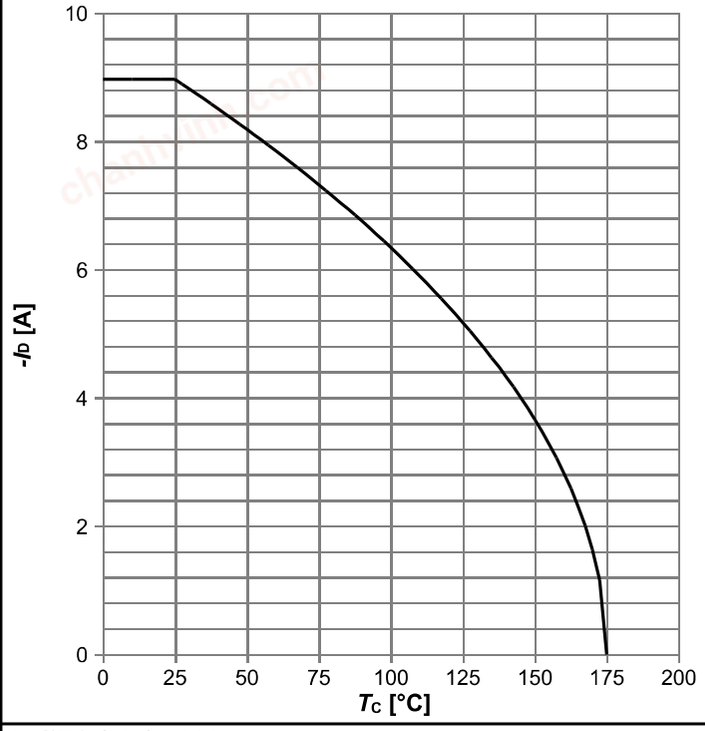
4 Electrical characteristics diagrams

Diagram 1: Power dissipation



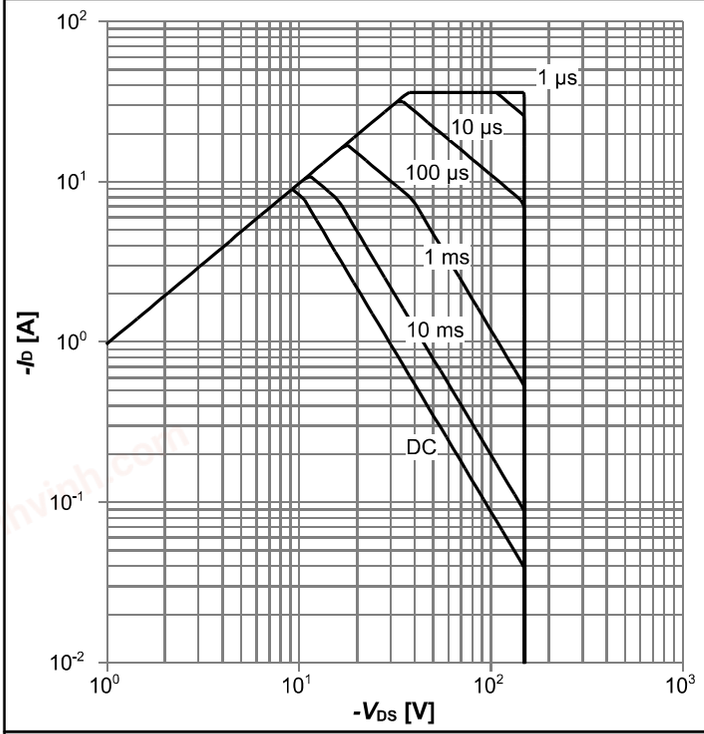
$P_{tot}=f(T_C)$

Diagram 2: Drain current



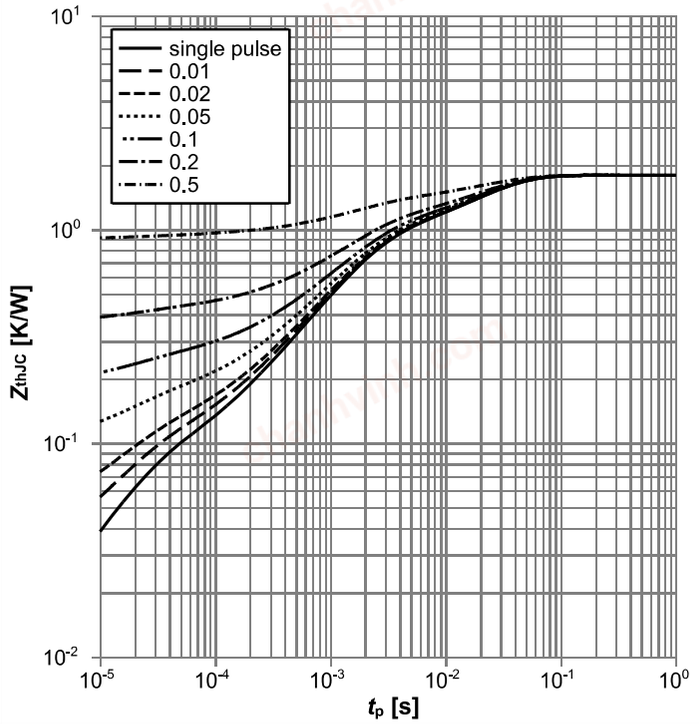
$I_D=f(T_C)$; $|V_{GS}|\geq 10$ V

Diagram 3: Safe operating area



$I_D=f(V_{DS})$; $T_C=25$ °C; $D=0$; parameter: t_p

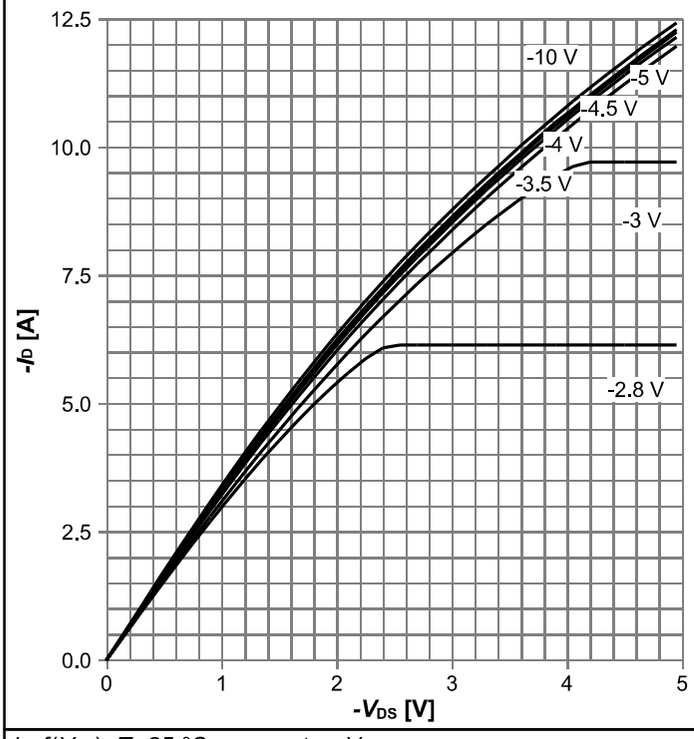
Diagram 4: Max. transient thermal impedance



$Z_{thJC}=f(t_p)$; parameter: $D=t_p/T$

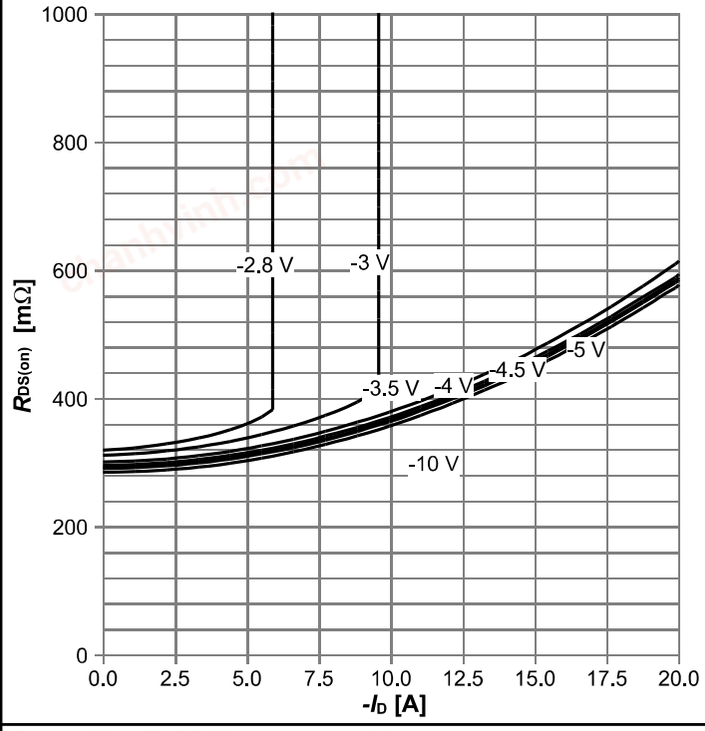
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Diagram 5: Typ. output characteristics



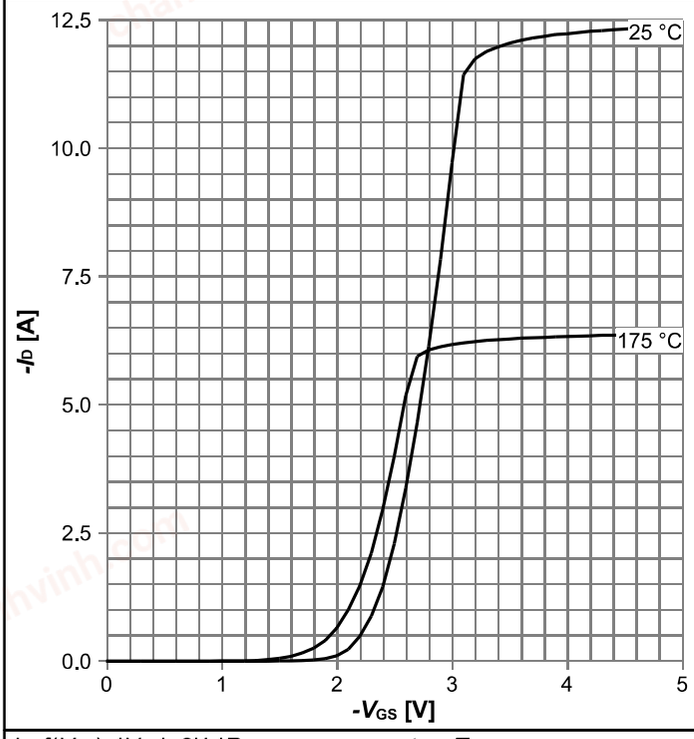
I_D=f(V_{DS}), T_j=25 °C; parameter: V_{GS}

Diagram 6: Typ. drain-source on resistance



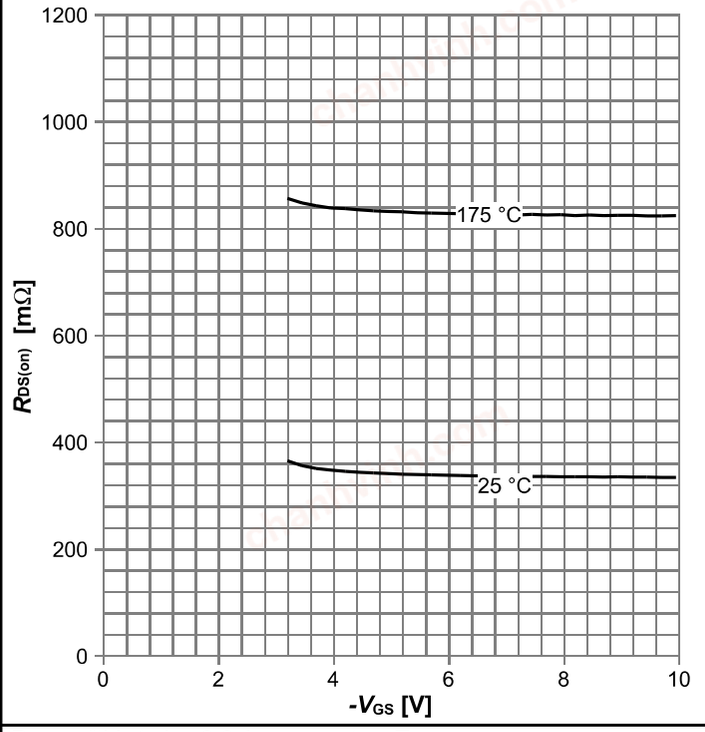
$R_{DS(on)}$=f(I_D), T_j=25 °C; parameter: V_{GS}

Diagram 7: Typ. transfer characteristics



I_D=f(V_{GS}), |V_{DS}|>2|I_D|$R_{DS(on)max}$; parameter: T_j

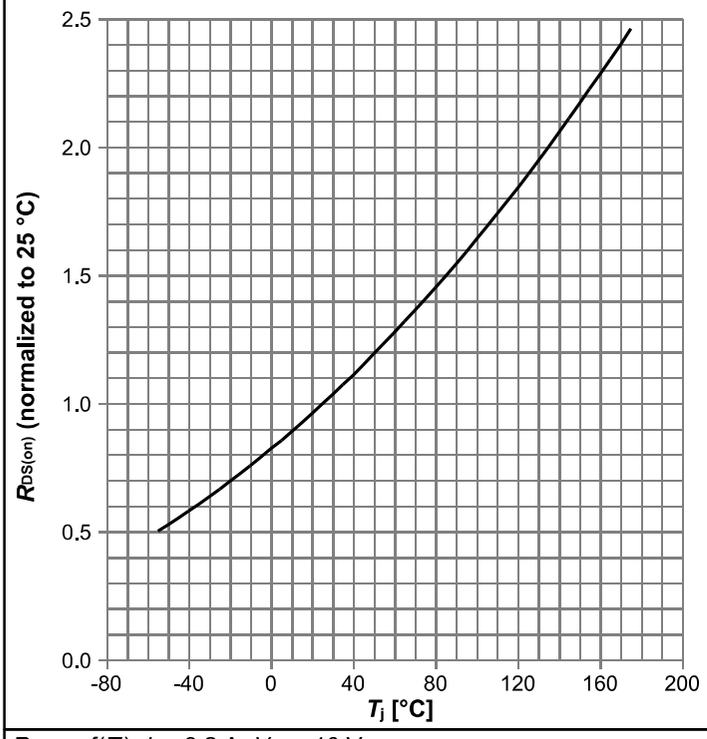
Diagram 8: Typ. drain-source on resistance



$R_{DS(on)}$=f(V_{GS}), I_D=-8.2 A; parameter: T_j

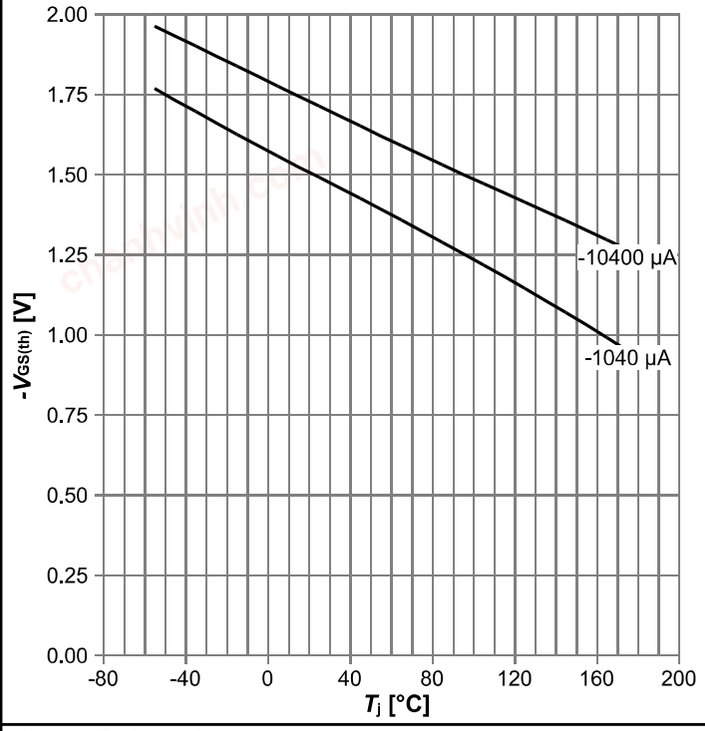
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Diagram 9: Normalized drain-source on resistance



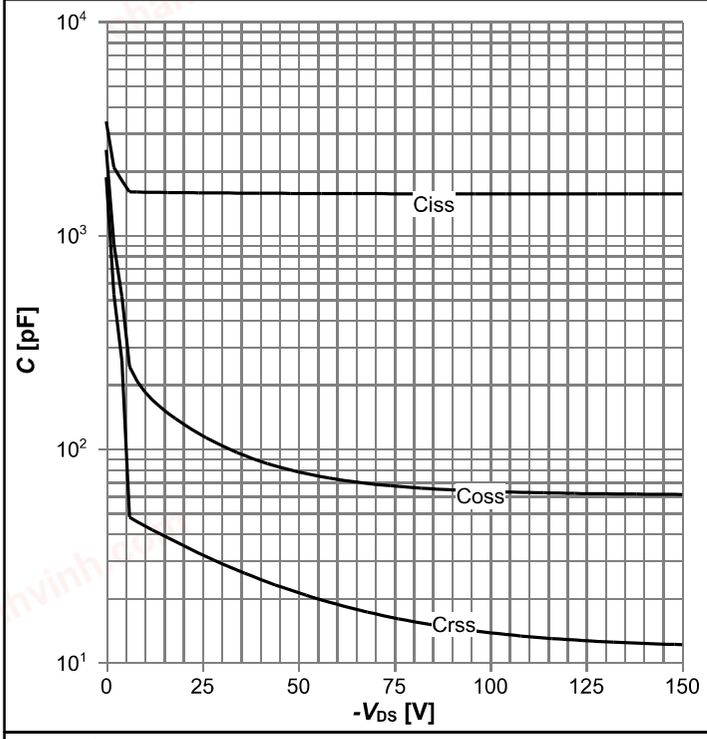
$R_{DS(on)}$=f(T_j), I_D=-8.2 A, V_{GS}=-10 V

Diagram 10: Typ. gate threshold voltage



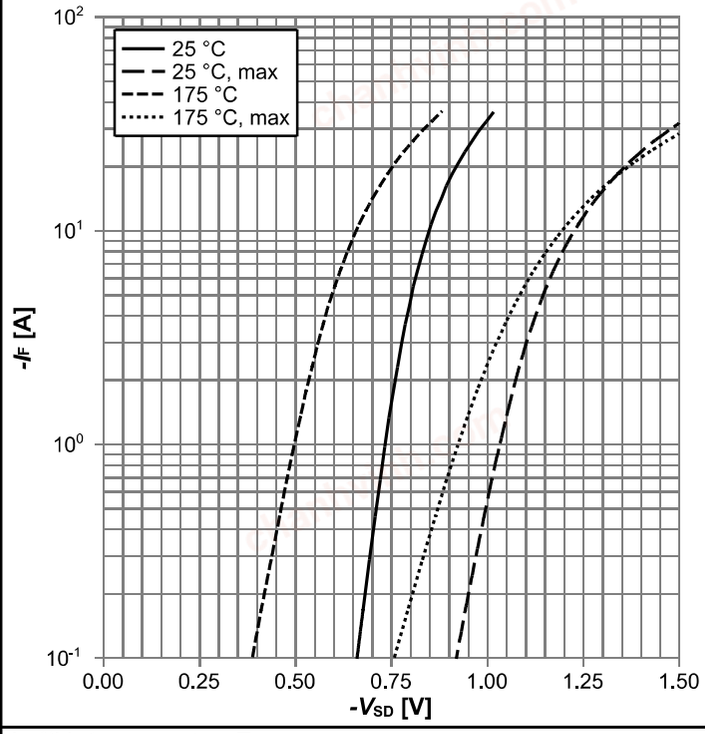
$V_{GS(th)}$=f(T_j), V_{GS}=V_{DS}; parameter: I_D

Diagram 11: Typ. capacitances



C=f(V_{DS}); V_{GS}=0 V; f=1 MHz

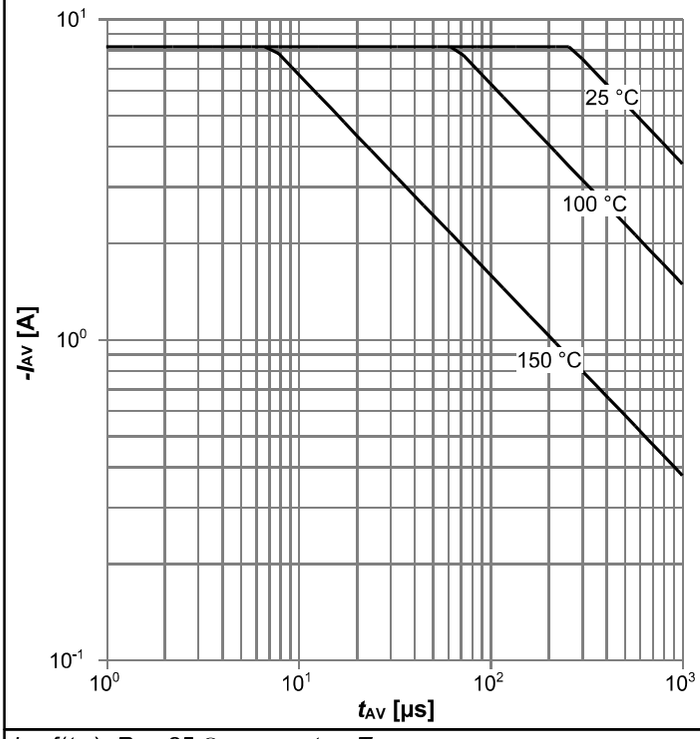
Diagram 12: Forward characteristics of reverse diode



I_F=f(V_{SD}); parameter: T_j

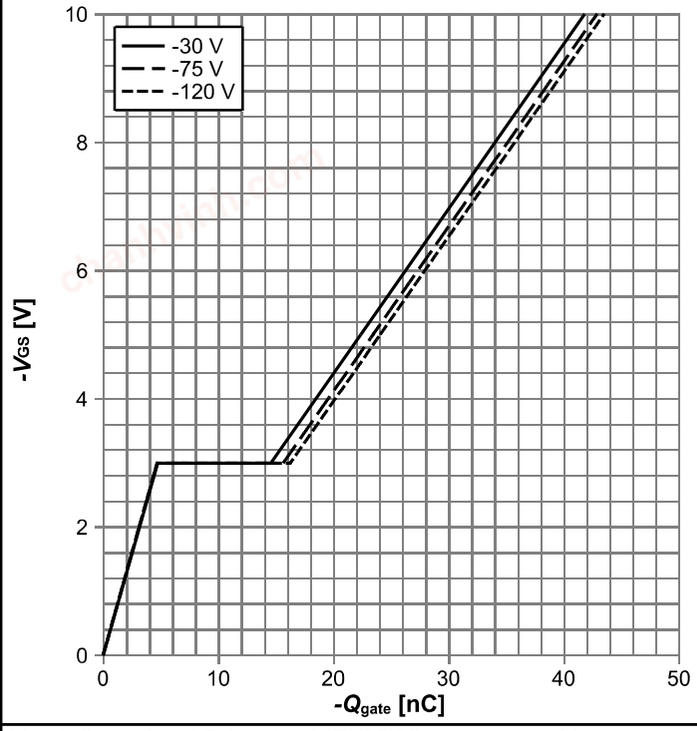
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Diagram 13: Avalanche characteristics



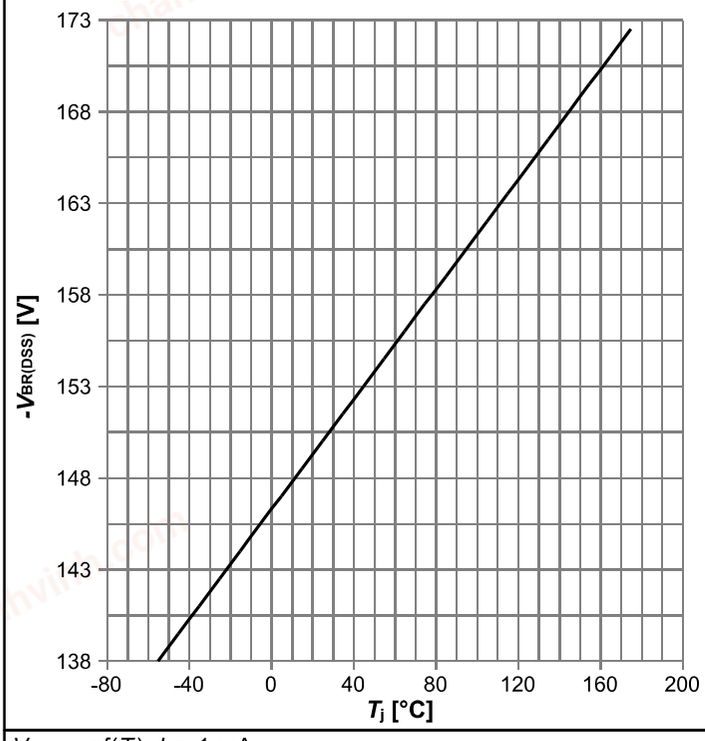
I_{AS}=f(t_{AV}); R_{GS}=25 Ω; parameter: $T_{j,start}$

Diagram 14: Typ. gate charge



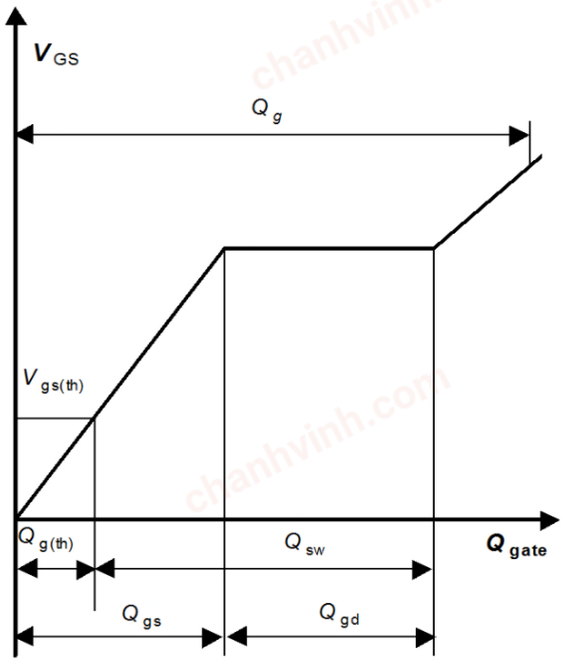
V_{GS}=f(Q_{gate}), I_D=-8.2 A pulsed, T_j=25 °C; parameter: V_{DD}

Diagram 15: Drain-source breakdown voltage



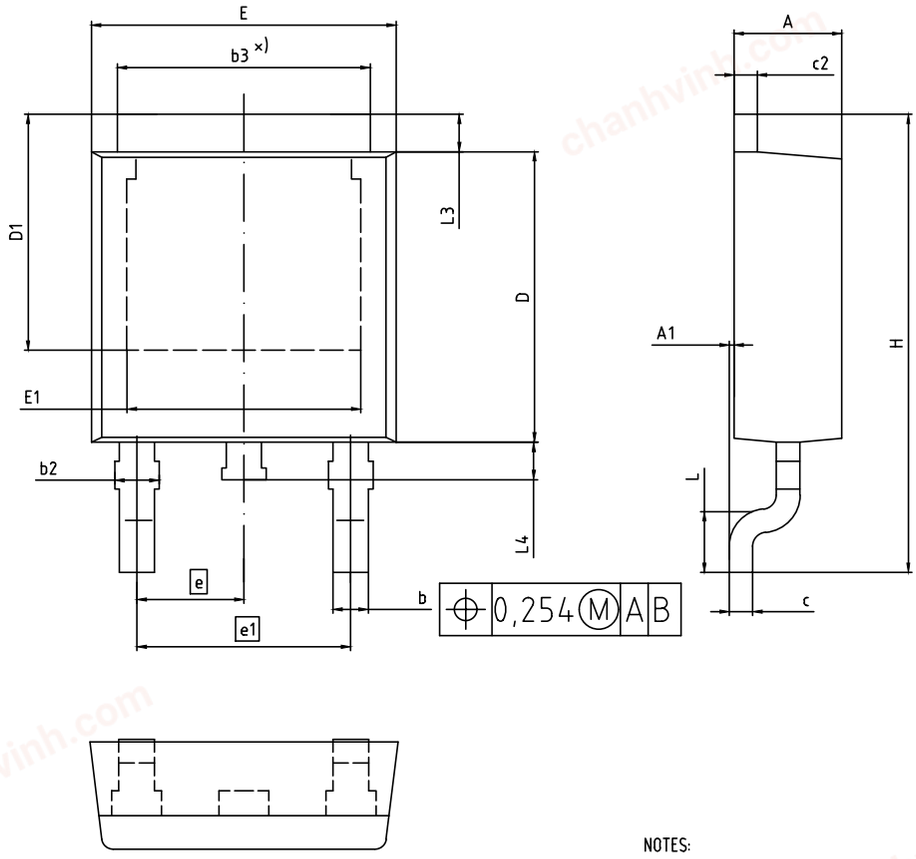
$V_{BR(DSS)}$=f(T_j); I_D=-1 mA

Diagram Gate charge waveforms



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5 Package Outlines



NOTES:

1. INDUSTRIAL QUALITY GRADE
2. ALL DIMENSIONS REFER TO JEDEC STANDARD TO-252 DO NOT INCLUDE MOLD FLASH OR PROTRUSIONS.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	2,16	2,41	0,085	0,095
A1	0.00	0.15	0.000	0.006
b	0.64	0.89	0.025	0.035
b2	0,65	1,15	0,026	0,045
b3	4,95	5,50	0,195	0,217
c	0.46	0.61	0.018	0.024
c2	0.40	0.98	0.016	0.039
D	5,97	6,22	0,235	0,245
D1	5,02	5,84	0,198	0,230
E	6,35	6,73	0,250	0,265
E1	4.32	5.21	0.185	0.205
e	2.29 (BSC)		0.090 (BSC)	
e1	4.57 (BSC)		0.180 (BSC)	
N	3		3	
H	9,40	10,48	0,370	0,413
L	1,18	1,78	0,046	0,070
L3	0.89	1.27	0.035	0.050
L4	0.51	1.02	0.020	0.040

DOCUMENT NO.
Z8B00003328

SCALE 0 2.5 0 2.5 5mm

EUROPEAN PROJECTION

ISSUE DATE
05-02-2016

REVISION
06

Figure 1 Outline PG-TO252-3, dimensions in mm/inches

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Revision History

IPD42DP15LM

Revision: 2021-05-10, Rev. 2.0

Previous Revision

Revision	Date	Subjects (major changes since last revision)
2.0	2021-05-10	Release of final version

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